Lattice Semiconductor Corporation - LFE3-17EA-6FTN256I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

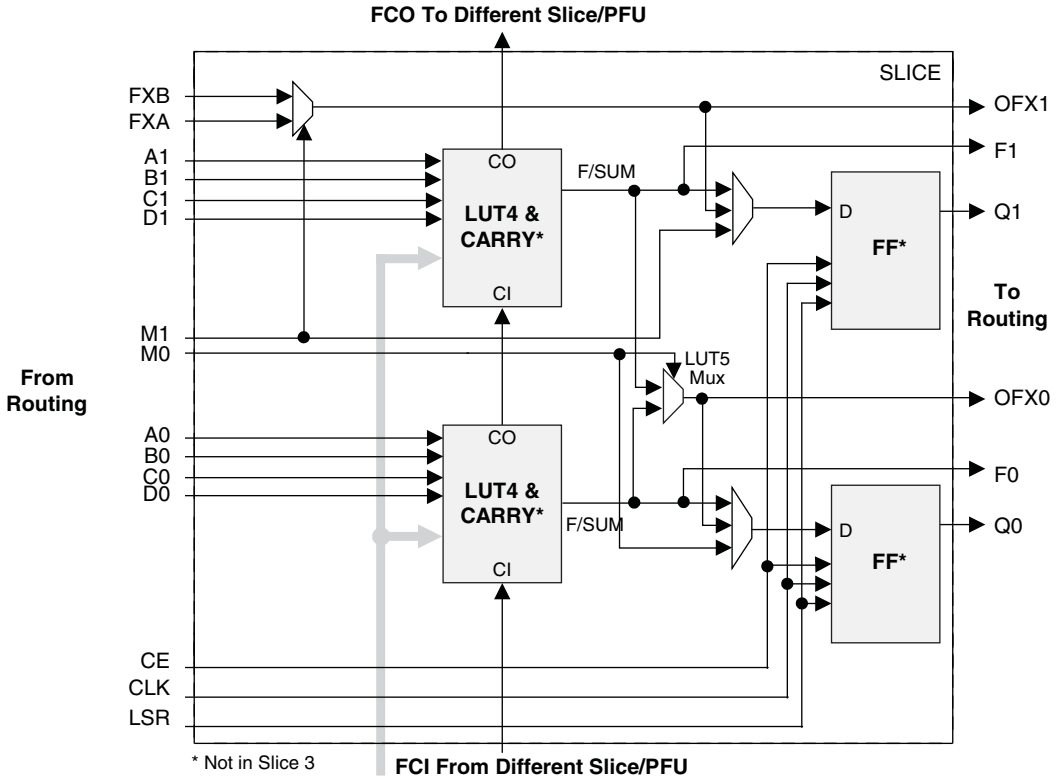
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	716800
Number of I/O	133
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-BGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-17ea-6ftn256i

Figure 2-3. Slice Diagram



For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:

WCK is CLK
WRE is from LSR
DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
WAD [A:D] is a 4-bit address from slice 2 LUT input

Table 2-2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FC	Fast Carry-in[1]
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6 and LUT7
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6 and LUT7
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8[2] MUX depending on the slice
Output	Inter-PFU signal	FCO	Slice 2 of each PFU is the fast carry chain output[1]

1. See Figure 2-3 for connection details.
2. Requires two PFUs.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals. A 16x2-bit pseudo dual port RAM (PDPR) memory is created by using one Slice as the read-write port and the other companion slice as the read-only port.

LatticeECP3 devices support distributed memory initialization.

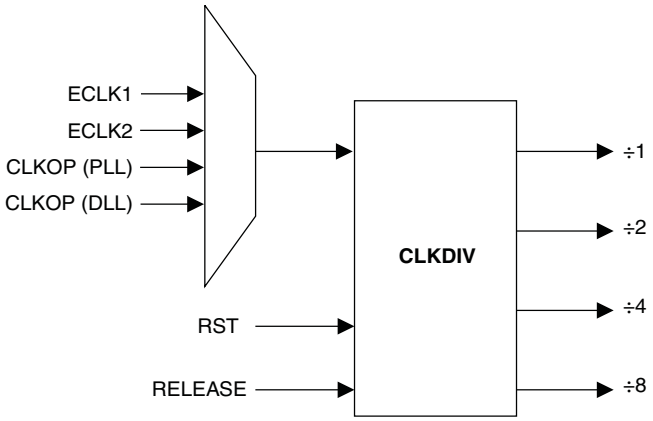
The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in LatticeECP3 devices, please see TN1179, LatticeECP3 Memory Usage Guide.

Table 2-3. Number of Slices Required to Implement Distributed RAM

	SPR 16X4	PDPR 16X4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Figure 2-8. Clock Divider Connections



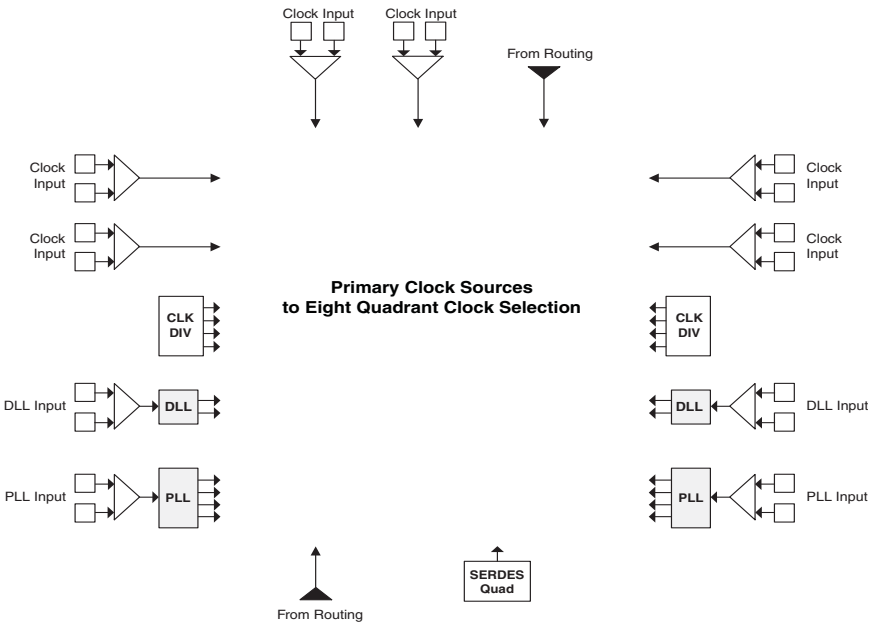
Clock Distribution Network

LatticeECP3 devices have eight quadrant-based primary clocks and eight secondary clock/control sources. Two high performance edge clocks are available on the top, left, and right edges of the device to support high speed interfaces. These clock sources are selected from external I/Os, the sysCLOCK PLLs, DLLs or routing. These clock sources are fed throughout the chip via a clock distribution system.

Primary Clock Sources

LatticeECP3 devices derive clocks from six primary source types: PLL outputs, DLL outputs, CLKDIV outputs, dedicated clock inputs, routing and SERDES Quads. LatticeECP3 devices have two to ten sysCLOCK PLLs and two DLLs, located on the left and right sides of the device. There are six dedicated clock inputs: two on the top side, two on the left side and two on the right side of the device. Figures 2-9, 2-10 and 2-11 show the primary clock sources for LatticeECP3 devices.

Figure 2-9. Primary Clock Sources for LatticeECP3-17



Note: Clock inputs can be configured in differential or single-ended mode.

MAC DSP Element

In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice in the LatticeECP3 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-27 shows the MAC sysDSP element.

Figure 2-27. MAC DSP Element

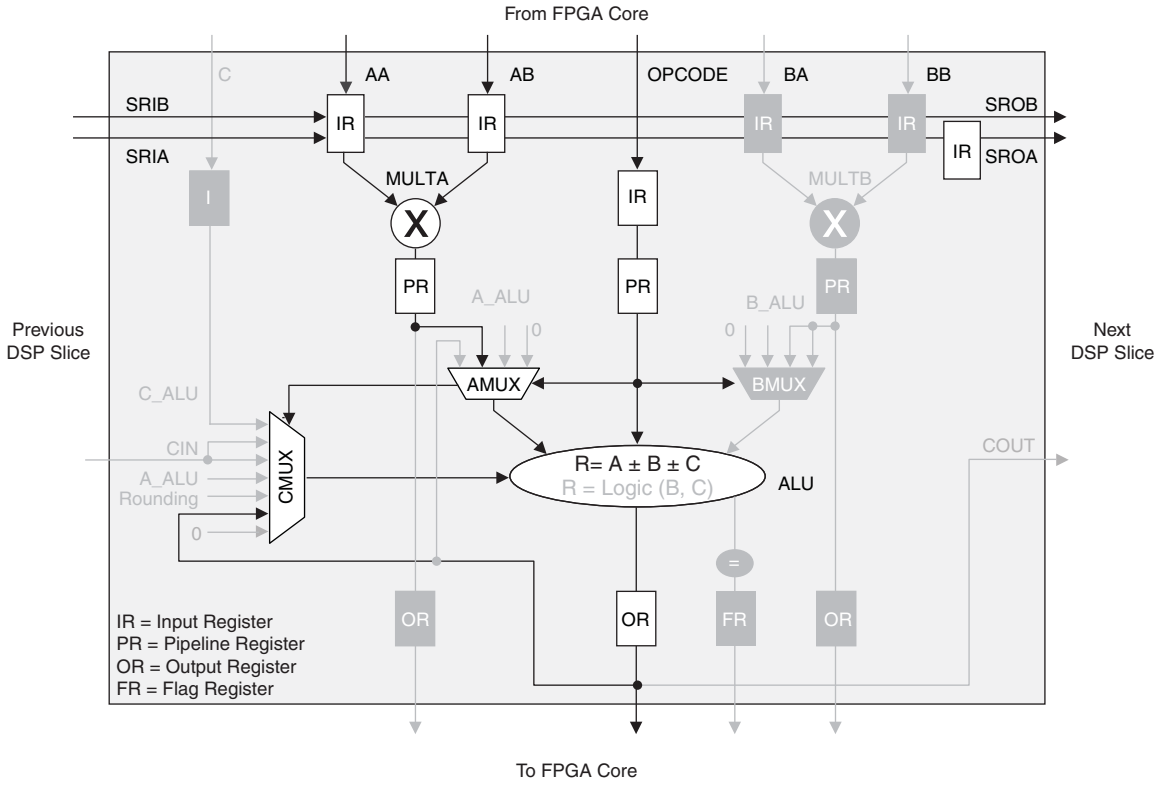
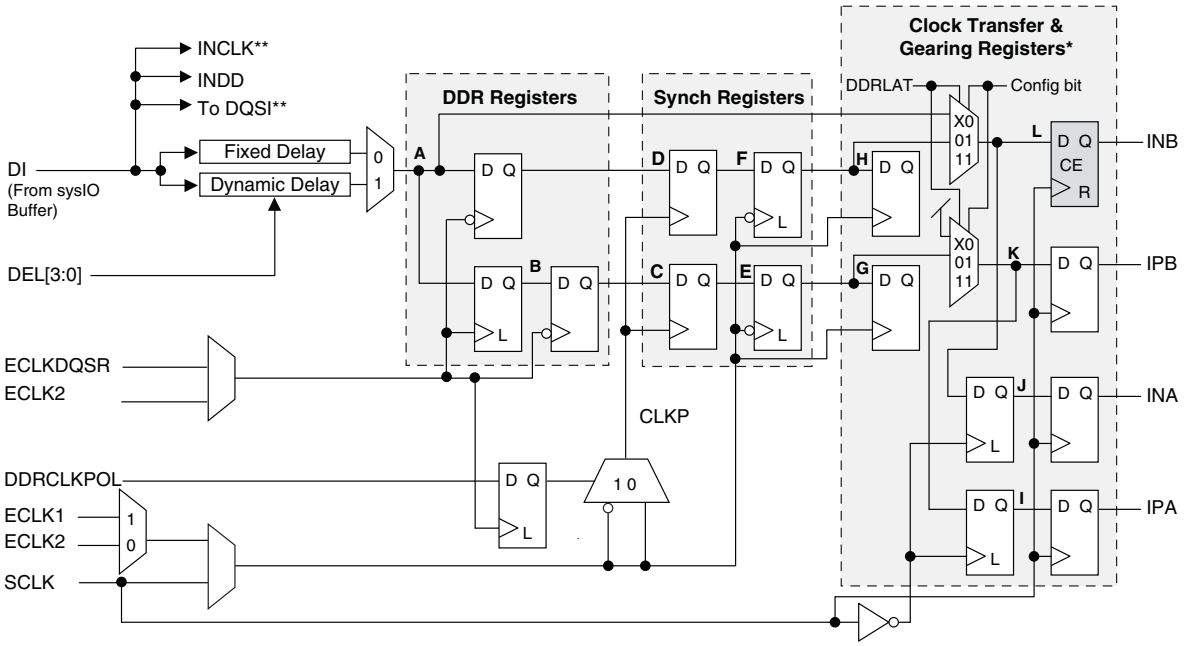


Figure 2-33. Input Register Block for Left, Right and Top Edges



* Only on the left and right sides.
** Selected PIO.
Note: Simplified diagram does not show CE/SET/REST details.

Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysI/O buffers. The blocks on the left and right PIOs contain registers for SDR and full DDR operation. The topside PIO block is the same as the left and right sides except it does not support ODDRX2 gearing of output logic. ODDRX2 gearing is used in DDR3 memory interfaces.The PIO blocks on the bottom contain the SDR registers but do not support generic DDR.

Figure 2-34 shows the Output Register Block for PIOs on the left and right edges.

In SDR mode, OPOSA feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, two of the inputs are fed into registers on the positive edge of the clock. At the next clock cycle, one of the registered outputs is also latched.

A multiplexer running off the same clock is used to switch the mux between the 11 and 01 inputs that will then feed the output.

A gearbox function can be implemented in the output register block that takes four data streams: OPOSA, ONEGA, OPOSB and ONEGB. All four data inputs are registered on the positive edge of the system clock and two of them are also latched. The data is then output at a high rate using a multiplexer that runs off the DQCLK0 and DQCLK1 clocks. DQCLK0 and DQCLK1 are used in this case to transfer data from the system clock to the edge clock domain. These signals are generated in the DQS Write Control Logic block. See Figure 2-37 for an overview of the DQS write control logic.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Further discussion on using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.

LatticeECP3 Supply Current (Standby)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical		Units
			–6L, –7L, –8L	–6, –7, –8	
I_{CC}	Core Power Supply Current	ECP-17EA	29.8	49.4	mA
		ECP3-35EA	53.7	89.4	mA
		ECP3-70EA	137.3	230.7	mA
		ECP3-95EA	137.3	230.7	mA
		ECP3-150EA	219.5	370.9	mA
I_{CCAUX}	Auxiliary Power Supply Current	ECP-17EA	18.3	19.4	mA
		ECP3-35EA	19.6	23.1	mA
		ECP3-70EA	26.5	32.4	mA
		ECP3-95EA	26.5	32.4	mA
		ECP3-150EA	37.0	45.7	mA
I_{CCPLL}	PLL Power Supply Current (Per PLL)	ECP-17EA	0.0	0.0	mA
		ECP3-35EA	0.1	0.1	mA
		ECP3-70EA	0.1	0.1	mA
		ECP3-95EA	0.1	0.1	mA
		ECP3-150EA	0.1	0.1	mA
I_{CCIO}	Bank Power Supply Current (Per Bank)	ECP-17EA	1.3	1.4	mA
		ECP3-35EA	1.3	1.4	mA
		ECP3-70EA	1.4	1.5	mA
		ECP3-95EA	1.4	1.5	mA
		ECP3-150EA	1.4	1.5	mA
I_{CCJ}	JTAG Power Supply Current	All Devices	2.5	2.5	mA
I_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	ECP-17EA	6.1	6.1	mA
		ECP3-35EA	6.1	6.1	mA
		ECP3-70EA	18.3	18.3	mA
		ECP3-95EA	18.3	18.3	mA
		ECP3-150EA	24.4	24.4	mA

1. For further information on supply current, please see the list of technical documentation at the end of this data sheet.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
3. Frequency 0 MHz.
4. Pattern represents a “blank” configuration data file.
5. T_J = 85 °C, power supplies at nominal voltage.
6. To determine the LatticeECP3 peak start-up current data, use the Power Calculator tool.

sysI/O Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS33[2]	3.135	3.3	3.465	—	—	—
LVCMOS33D	3.135	3.3	3.465	—	—	—
LVCMOS25[2]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[2]	1.14	1.2	1.26	—	—	—
LVTTL33[2]	3.135	3.3	3.465	—	—	—
PCI33	3.135	3.3	3.465	—	—	—
SSTL15[3]	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I, II[2]	2.375	2.5	2.625	1.15	1.25	1.35
SSTL33_I, II[2]	3.135	3.3	3.465	1.3	1.5	1.7
HSTL15_I[2]	1.425	1.5	1.575	0.68	0.75	0.9
HSTL18_I, II[2]	1.71	1.8	1.89	0.816	0.9	1.08
LVDS25[2]	2.375	2.5	2.625	—	—	—
LVDS25E	2.375	2.5	2.625	—	—	—
MLVDS[1]	2.375	2.5	2.625	—	—	—
LVPECL33[1, 2]	3.135	3.3	3.465	—	—	—
Mini LVDS	2.375	2.5	2.625	—	—	—
BLVDS25[1, 2]	2.375	2.5	2.625	—	—	—
RSDS[2]	2.375	2.5	2.625	—	—	—
RSDSE[1, 2]	2.375	2.5	2.625	—	—	—
TRLVDS	3.14	3.3	3.47	—	—	—
PPLVDS	3.14/2.25	3.3/2.5	3.47/2.75	—	—	—
SSTL15D[3]	1.43	1.5	1.57	—	—	—
SSTL18D_I[2, 3], II[2, 3]	1.71	1.8	1.89	—	—	—
SSTL25D_ I[2], II[2]	2.375	2.5	2.625	—	—	—
SSTL33D_ I[2], II[2]	3.135	3.3	3.465	—	—	—
HSTL15D_ I[2]	1.425	1.5	1.575	—	—	—
HSTL18D_ I[2], II[2]	1.71	1.8	1.89	—	—	—

1. Inputs on chip. Outputs are implemented with the addition of external resistors.
2. For input voltage compatibility, see TN1177, LatticeECP3 sysIO Usage Guide.
3. VREF is required when using Differential SSTL to interface to DDR memory.

sysI/O Single-Ended DC Electrical Characteristics

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)				
LVCMOS33	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, -8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS25	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS18	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	–16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS15	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	8, 4	–8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS12	–0.3	0.35 V_{CC}	0.65 V_{CC}	3.6	0.4	V_{CCIO} - 0.4	6, 2	–6, –2
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVTTL33	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
PCI33	–0.3	0.3 V_{CCIO}	0.5 V_{CCIO}	3.6	0.1 V_{CCIO}	0.9 V_{CCIO}	1.5	–0.5
SSTL18_I	–0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.4	V_{CCIO} - 0.4	6.7	–6.7
SSTL18_II (DDR2 Memory)	–0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.28	V_{CCIO} - 0.28	8	–8
							11	–11
SSTL2_I	–0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	7.6	–7.6
							12	–12
SSTL2_II (DDR Memory)	–0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.35	V_{CCIO} - 0.43	15.2	–15.2
							20	–20
SSTL3_I	–0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.7	V_{CCIO} - 1.1	8	–8
SSTL3_II	–0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.5	V_{CCIO} - 0.9	16	–16
SSTL15 (DDR3 Memory)	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.3	V_{CCIO} - 0.3	7.5	–7.5
						V_{CCIO} * 0.8	9	–9
HSTL15_I	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
HSTL18_I	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	8	–8
							12	–12
HSTL18_II	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	16	–16

1. For electromigration, the average DC current drawn by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed n * 8 mA, where n is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

MLVDS25

The LatticeECP3 devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-5 is one possible solution for MLVDS standard implementation. Resistor values in Figure 3-5 are industry standard values for 1% resistors.

Figure 3-5. MLVDS25 (Multipoint Low Voltage Differential Signaling)

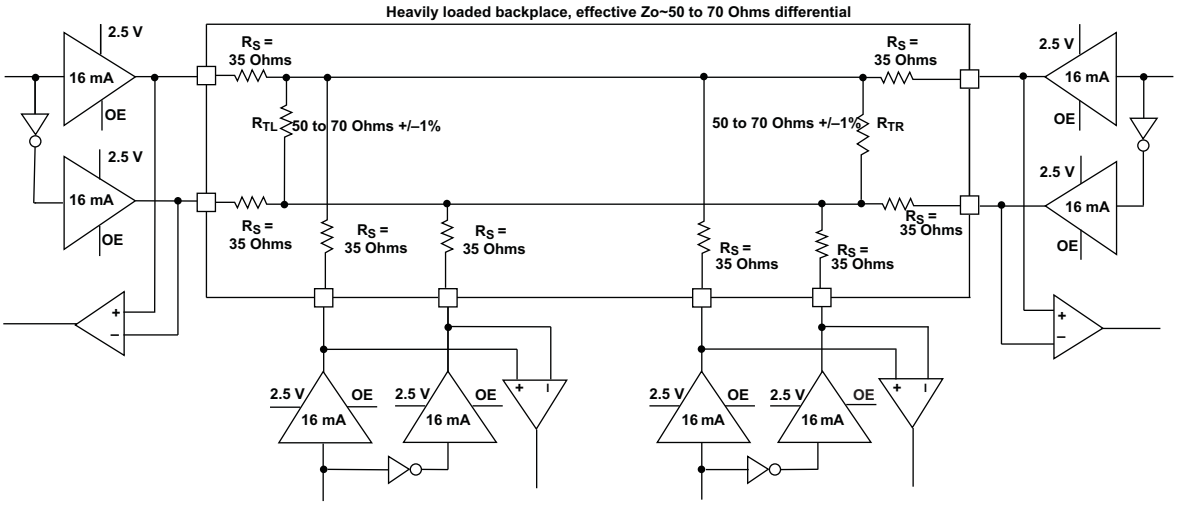


Table 3-5. MLVDS25 DC Conditions[1]

Parameter	Description	Typical		Units
		Zo=50Ω	Zo=70Ω	
V_{CCIO}	Output Driver Supply (+/–5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/–1%)	35.00	35.00	Ω
R_{TL}	Driver Parallel Resistor (+/–1%)	50.00	70.00	Ω
R_{TR}	Receiver Termination (+/–1%)	50.00	70.00	Ω
V_{OH}	Output High Voltage	1.52	1.60	V
V_{OL}	Output Low Voltage	0.98	0.90	V
V_{OD}	Output Differential Voltage	0.54	0.70	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	21.74	20.00	mA

1. For input buffer, see LVDS table.

Register-to-Register Performance[1, 2, 3]

Function	–8 Timing	Units
18x18 Multiply/Accumulate (Input & Output Registers)	200	MHz
18x18 Multiply-Add/Sub (All Registers)	400	MHz

1. These timing numbers were generated using ispLEVER tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. For details on -9 speed grade devices, please contact your Lattice Sales Representative.

Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond and ispLEVER design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond and ispLEVER design tools can provide logic timing numbers at a particular temperature and voltage.

Figure 3-6. Generic DDRX1/DDRX2 (With Clock and Data Edges Aligned)

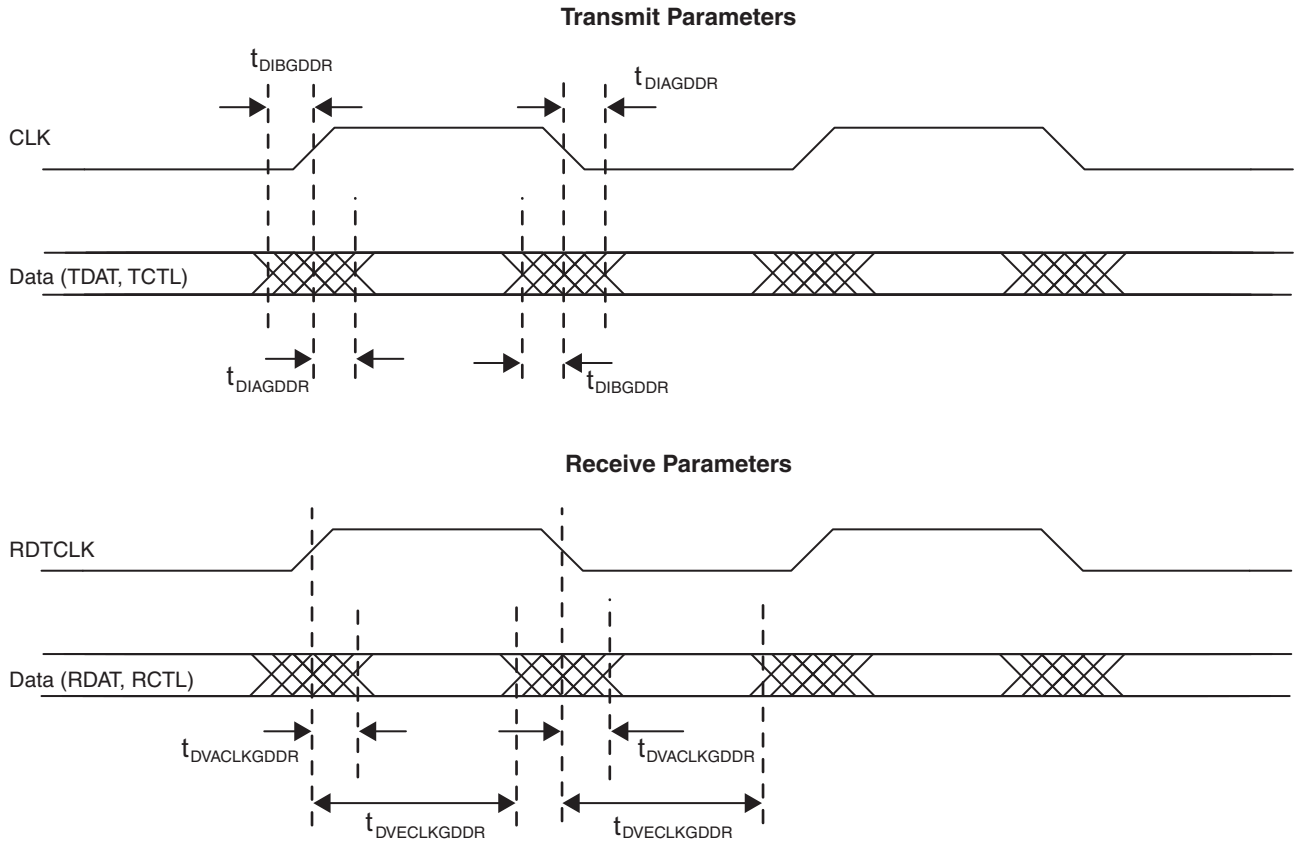
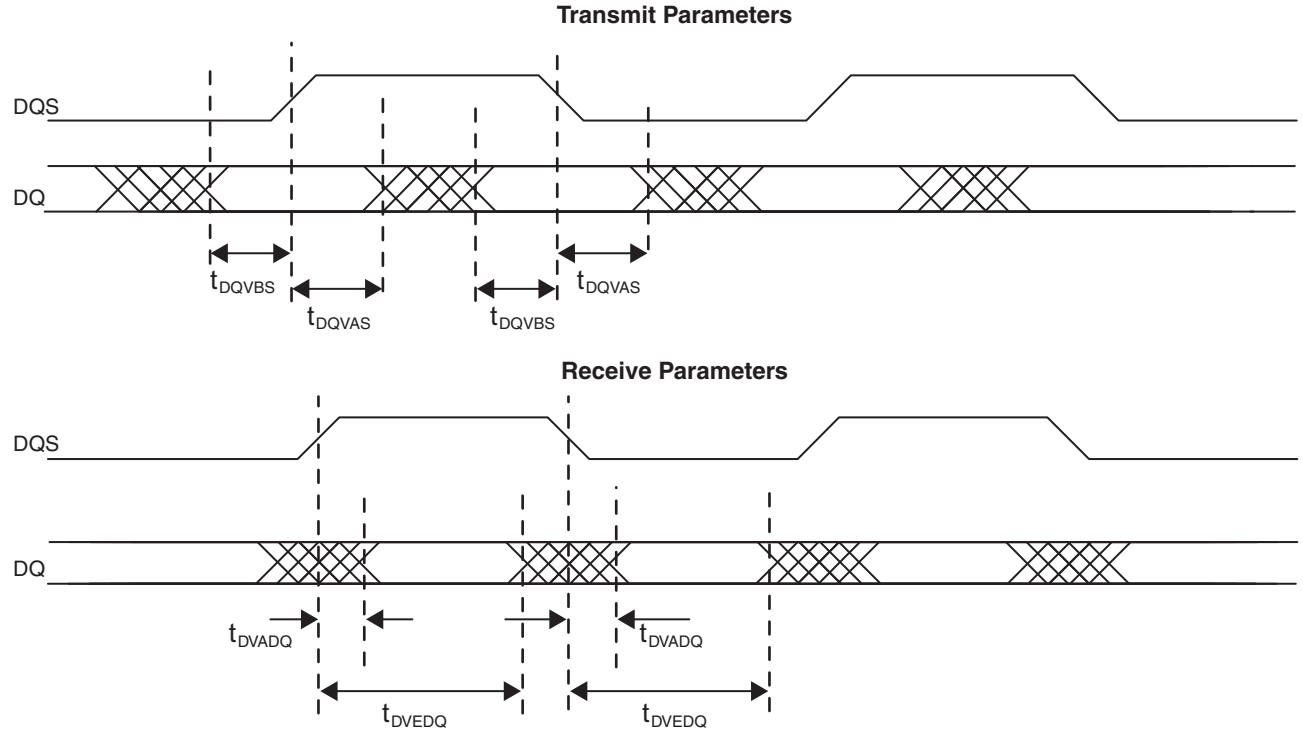


Figure 3-7. DDR/DDR2/DDR3 Parameters



LatticeECP3 Internal Switching Characteristics[1, 2, 5]

Over Recommended Commercial Operating Conditions

Parameter	Description	–8		–7		–6		Units.
		Min.	Max.	Min.	Max.	Min.	Max.	
PFU/PFF Logic Mode Timing								
t_{LUT4_PFU}	LUT4 delay (A to D inputs to F output)	—	0.147	—	0.163	—	0.179	ns
t_{LUT6_PFU}	LUT6 delay (A to D inputs to OFX output)	—	0.281	—	0.335	—	0.379	ns
t_{LSR_PFU}	Set/Reset to output of PFU (Asynchronous)	—	0.593	—	0.674	—	0.756	ns
t_{LSRREC_PFU}	Asynchronous Set/Reset recovery time for PFU Logic		0.298		0.345		0.391	ns
t_{SUM_PFU}	Clock to Mux (M0,M1) Input Setup Time	0.134	—	0.144	—	0.153	—	ns
t_{HM_PFU}	Clock to Mux (M0,M1) Input Hold Time	–0.097	—	–0.103	—	–0.109	—	ns
t_{SUD_PFU}	Clock to D input setup time	0.061	—	0.068	—	0.075	—	ns
t_{HD_PFU}	Clock to D input hold time	0.019	—	0.013	—	0.015	—	ns
t_{CK2Q_PFU}	Clock to Q delay, (D-type Register Configuration)	—	0.243	—	0.273	—	0.303	ns
PFU Dual Port Memory Mode Timing								
t_{CORAM_PFU}	Clock to Output (F Port)	—	0.710	—	0.803	—	0.897	ns
t_{SUDATA_PFU}	Data Setup Time	–0.137	—	–0.155	—	–0.174	—	ns
t_{HDATA_PFU}	Data Hold Time	0.188	—	0.217	—	0.246	—	ns
t_{SUADDR_PFU}	Address Setup Time	–0.227	—	–0.257	—	–0.286	—	ns
t_{HADDR_PFU}	Address Hold Time	0.240	—	0.275	—	0.310	—	ns
t_{SUWREN_PFU}	Write/Read Enable Setup Time	–0.055	—	–0.055	—	–0.063	—	ns
t_{HWREN_PFU}	Write/Read Enable Hold Time	0.059	—	0.059	—	0.071	—	ns
PIC Timing								
PIO Input/Output Buffer Timing								
t_{IN_PIO}	Input Buffer Delay (LVCMOS25)	—	0.423	—	0.466	—	0.508	ns
t_{OUT_PIO}	Output Buffer Delay (LVCMOS25)	—	1.241	—	1.301	—	1.361	ns
IOLOGIC Input/Output Timing								
t_{SUI_PIO}	Input Register Setup Time (Data Before Clock)	0.956	—	1.124	—	1.293	—	ns
t_{HI_PIO}	Input Register Hold Time (Data after Clock)	0.225	—	0.184	—	0.240	—	ns
t_{COO_PIO}	Output Register Clock to Output Delay[4]	-	1.09	-	1.16	-	1.23	ns
t_{SUCE_PIO}	Input Register Clock Enable Setup Time	0.220	—	0.185	—	0.150	—	ns
t_{HCE_PIO}	Input Register Clock Enable Hold Time	–0.085	—	–0.072	—	–0.058	—	ns
t_{SULSR_PIO}	Set/Reset Setup Time	0.117	—	0.103	—	0.088	—	ns
t_{HLSR_PIO}	Set/Reset Hold Time	–0.107	—	–0.094	—	–0.081	—	ns
EBR Timing								
t_{CO_EBR}	Clock (Read) to output from Address or Data	—	2.78	—	2.89	—	2.99	ns
t_{COO_EBR}	Clock (Write) to output from EBR output Register	—	0.31	—	0.32	—	0.33	ns
t_{SUDATA_EBR}	Setup Data to EBR Memory	–0.218	—	–0.227	—	–0.237	—	ns
t_{HDATA_EBR}	Hold Data to EBR Memory	0.249	—	0.257	—	0.265	—	ns
t_{SUADDR_EBR}	Setup Address to EBR Memory	–0.071	—	–0.070	—	–0.068	—	ns
t_{HADDR_EBR}	Hold Address to EBR Memory	0.118	—	0.098	—	0.077	—	ns
t_{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory	–0.107	—	–0.106	—	–0.106	—	ns

LatticeECP3 Family Timing Adders[1, 2, 3, 4, 5, 7]

Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
Input Adjusters					
LVDS25E	LVDS, Emulated, VCCIO = 2.5 V	0.03	–0.01	–0.03	ns
LVDS25	LVDS, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
BLVDS25	BLVDS, Emulated, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
MLVDS25	MLVDS, Emulated, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
RSDS25	RSDS, VCCIO = 2.5 V	0.03	–0.01	–0.03	ns
PPLVDS	Point-to-Point LVDS	0.03	–0.01	–0.03	ns
TRLVDS	Transition-Reduced LVDS	0.03	0.00	–0.04	ns
Mini MLVDS	Mini LVDS	0.03	–0.01	–0.03	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.17	0.23	0.28	ns
HSTL18_I	HSTL_18 class I, VCCIO = 1.8 V	0.20	0.17	0.13	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.20	0.17	0.13	ns
HSTL18D_I	Differential HSTL 18 class I	0.20	0.17	0.13	ns
HSTL18D_II	Differential HSTL 18 class II	0.20	0.17	0.13	ns
HSTL15_I	HSTL_15 class I, VCCIO = 1.5 V	0.10	0.12	0.13	ns
HSTL15D_I	Differential HSTL 15 class I	0.10	0.12	0.13	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	0.17	0.23	0.28	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	0.17	0.23	0.28	ns
SSTL33D_I	Differential SSTL_3 class I	0.17	0.23	0.28	ns
SSTL33D_II	Differential SSTL_3 class II	0.17	0.23	0.28	ns
SSTL25_I	SSTL_2 class I, VCCIO = 2.5 V	0.12	0.14	0.16	ns
SSTL25_II	SSTL_2 class II, VCCIO = 2.5 V	0.12	0.14	0.16	ns
SSTL25D_I	Differential SSTL_2 class I	0.12	0.14	0.16	ns
SSTL25D_II	Differential SSTL_2 class II	0.12	0.14	0.16	ns
SSTL18_I	SSTL_18 class I, VCCIO = 1.8 V	0.08	0.06	0.04	ns
SSTL18_II	SSTL_18 class II, VCCIO = 1.8 V	0.08	0.06	0.04	ns
SSTL18D_I	Differential SSTL_18 class I	0.08	0.06	0.04	ns
SSTL18D_II	Differential SSTL_18 class II	0.08	0.06	0.04	ns
SSTL15	SSTL_15, VCCIO = 1.5 V	0.087	0.059	0.032	ns
SSTL15D	Differential SSTL_15	0.087	0.059	0.032	ns
LVTTL33	LVTTL, VCCIO = 3.3 V	0.07	0.07	0.07	ns
LVCMOS33	LVCMOS, VCCIO = 3.3 V	0.07	0.07	0.07	ns
LVCMOS25	LVCMOS, VCCIO = 2.5 V	0.00	0.00	0.00	ns
LVCMOS18	LVCMOS, VCCIO = 1.8 V	–0.13	–0.13	–0.13	ns
LVCMOS15	LVCMOS, VCCIO = 1.5 V	–0.07	–0.07	–0.07	ns
LVCMOS12	LVCMOS, VCCIO = 1.2 V	–0.20	–0.19	–0.19	ns
PCI33	PCI, VCCIO = 3.3 V	0.07	0.07	0.07	ns
Output Adjusters					
LVDS25E	LVDS, Emulated, VCCIO = 2.5 V	1.02	1.14	1.26	ns
LVDS25	LVDS, VCCIO = 2.5 V	–0.11	–0.07	–0.03	ns
BLVDS25	BLVDS, Emulated, VCCIO = 2.5 V	1.01	1.13	1.25	ns
MLVDS25	MLVDS, Emulated, VCCIO = 2.5 V	1.01	1.13	1.25	ns

LatticeECP3 Maximum I/O Buffer Speed (Continued)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
PCI33	PCI, V_{CCIO} = 3.3 V	66	MHz

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in the Switching Test Conditions table of this document.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

SERDES High-Speed Data Transmitter[1]

Table 3-6. Serial Output Timing and Levels

Symbol	Description	Frequency	Min.	Typ.	Max.	Units
$V_{TX-DIFF-P-P-1.44}$	Differential swing (1.44 V setting)[1, 2]	0.15 to 3.125 Gbps	1150	1440	1730	mV, p-p
$V_{TX-DIFF-P-P-1.35}$	Differential swing (1.35 V setting)[1, 2]	0.15 to 3.125 Gbps	1080	1350	1620	mV, p-p
$V_{TX-DIFF-P-P-1.26}$	Differential swing (1.26 V setting)[1, 2]	0.15 to 3.125 Gbps	1000	1260	1510	mV, p-p
$V_{TX-DIFF-P-P-1.13}$	Differential swing (1.13 V setting)[1, 2]	0.15 to 3.125 Gbps	840	1130	1420	mV, p-p
$V_{TX-DIFF-P-P-1.04}$	Differential swing (1.04 V setting)[1, 2]	0.15 to 3.125 Gbps	780	1040	1300	mV, p-p
$V_{TX-DIFF-P-P-0.92}$	Differential swing (0.92 V setting)[1, 2]	0.15 to 3.125 Gbps	690	920	1150	mV, p-p
$V_{TX-DIFF-P-P-0.87}$	Differential swing (0.87 V setting)[1, 2]	0.15 to 3.125 Gbps	650	870	1090	mV, p-p
$V_{TX-DIFF-P-P-0.78}$	Differential swing (0.78 V setting)[1, 2]	0.15 to 3.125 Gbps	585	780	975	mV, p-p
$V_{TX-DIFF-P-P-0.64}$	Differential swing (0.64 V setting)[1, 2]	0.15 to 3.125 Gbps	480	640	800	mV, p-p
V_{OCM}	Output common mode voltage	—	V_{CCOB} –0.75	V_{CCOB} –0.60	V_{CCOB} –0.45	V
T_{TX-R}	Rise time (20% to 80%)	—	145	185	265	ps
T_{TX-F}	Fall time (80% to 20%)	—	145	185	265	ps
$Z_{TX-OI-SE}$	Output Impedance 50/75/HiZ Ohms (single ended)	—	–20%	50/75/ Hi Z	+20%	Ohms
R_{LTX-RL}	Return loss (with package)	—	10			dB
$T_{TX-INTRASKEW}$	Lane-to-lane TX skew within a SERDES quad block (intra-quad)	—	—	—	200	ps
$T_{TX-INTERSKEW}$[3]	Lane-to-lane skew between SERDES quad blocks (inter-quad)	—	—	—	1UI +200	ps

1. All measurements are with 50 Ohm impedance.
2. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for actual binary settings and the min-max range.
3. Inter-quad skew is between all SERDES channels on the device and requires the use of a low skew internal reference clock.

LatticeECP3 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description		Min.	Max.	Units
POR, Configuration Initialization, and Wakeup					
t_{ICFG}	Time from the Application of V_{CC}, V_{CCAUX} or V_{CCIO8}* (Whichever is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Master mode	—	23	ms
		Slave mode	—	6	ms
t_{VMC}	Time from t_{ICFG} to the Valid Master MCLK		—	5	µs
t_{PRGM}	PROGRAMN Low Time to Start Configuration		25	—	ns
t_{PRGMRJ}	PROGRAMN Pin Pulse Rejection		—	10	ns
$t_{DPPINIT}$	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
$t_{DPPDONE}$	Delay Time from PROGRAMN Low to DONE Low		—	37	ns
t_{DINIT}[1]	PROGRAMN High to INITN High Delay		—	1	ms
t_{MWC}	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t_{CZ}	MCLK From Active To Low To High-Z		—	300	ns
t_{IODISS}	User I/O Disable from PROGRAMN Low		—	100	ns
t_{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence		—	100	ns
All Configuration Modes					
t_{SUCDI}	Data Setup Time to CCLK/MCLK		5	—	ns
t_{HCDI}	Data Hold Time to CCLK/MCLK		1	—	ns
t_{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode		-0.2	12	ns
Slave Serial					
t_{SSCH}	CCLK Minimum High Pulse		5	—	ns
t_{SSCL}	CCLK Minimum Low Pulse		5	—	ns
f_{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave Parallel					
t_{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t_{HCS}	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t_{SUWD}	WRITEN Setup Time to CCLK/MCLK		7	—	ns
t_{HWD}	WRITEN Hold Time to CCLK/MCLK		1	—	ns
t_{DCB}	CCLK/MCLK to BUSY Delay Time		—	12	ns
t_{CORD}	CCLK to Out for Read Data		—	12	ns
t_{BSCH}	CCLK Minimum High Pulse		6	—	ns
t_{BSCL}	CCLK Minimum Low Pulse		6	—	ns
t_{BSCYC}	Byte Slave Cycle Time		30	—	ns
f_{CCLK}	CCLK/MCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave SPI					
t_{CFGX}	INITN High to MCLK Low		—	80	ns
t_{CSSPI}	INITN High to CSSPIN Low		0.2	2	µs
t_{SOCDO}	MCLK Low to Output Valid		—	15	ns
t_{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time		0.3		µs
f_{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
t_{SSCH}	CCLK Minimum High Pulse		5	—	ns

Figure 3-28. Master SPI Configuration Waveforms

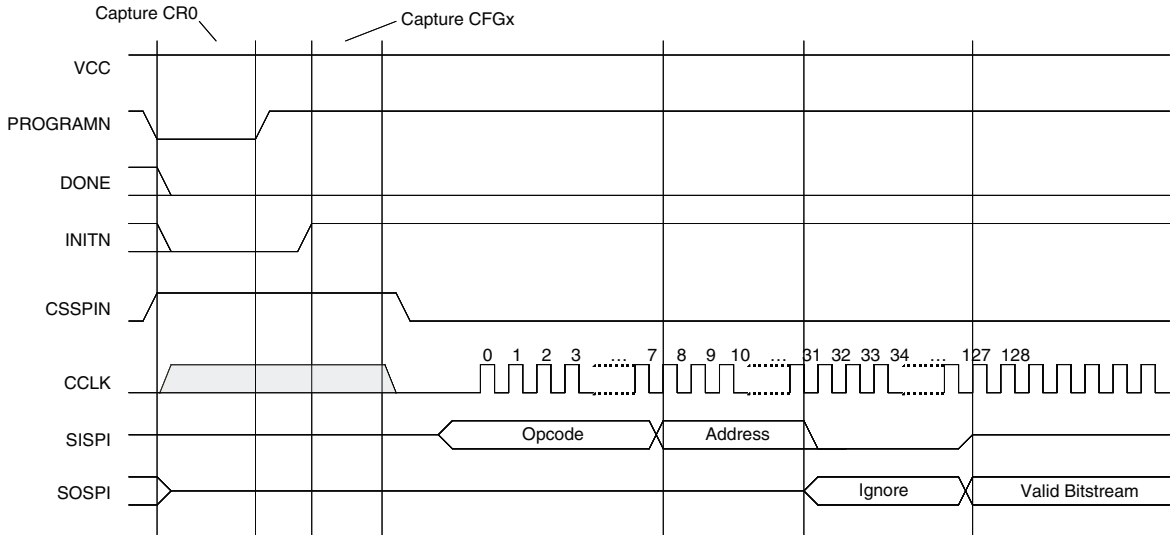
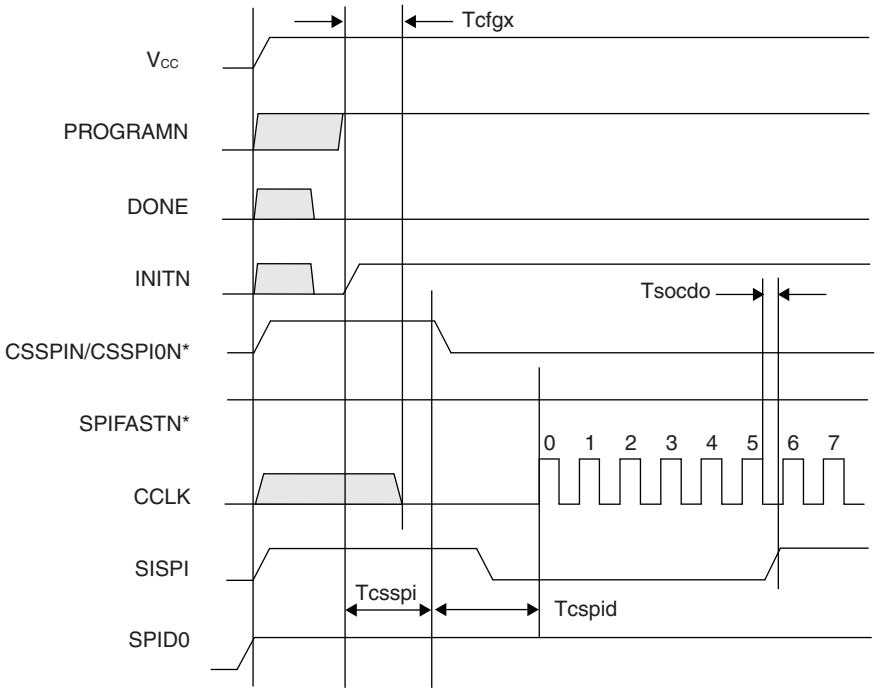


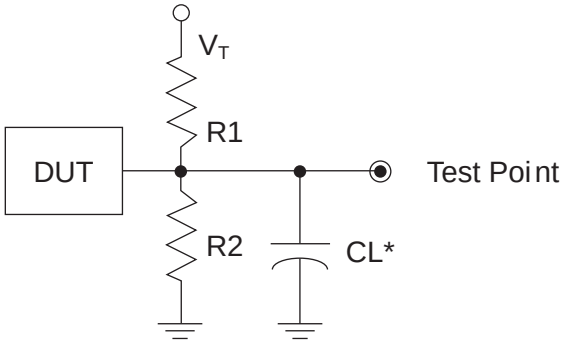
Figure 3-29. Master SPI POR Waveforms



Switching Test Conditions

Figure 3-33 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-23.

Figure 3-33. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-23. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0 pF	LVCMOS 3.3 = 1.5V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> H)	∞	1MΩ	0 pF	$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> L)	1 MΩ	∞	0 pF	$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H -> Z)	∞	100	0 pF	V_{OH} - 0.10	—
LVCMOS 2.5 I/O (L -> Z)	100	∞	0 pF	V_{OL} + 0.10	V_{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

LatticeECP3 Family Data Sheet Supplemental Information

For Further Information

A variety of technical notes for the LatticeECP3 family are available on the Lattice website at www.latticesemi.com.

- TN1169, LatticeECP3 sysCONFIG Usage Guide
- TN1176, LatticeECP3 SERDES/PCS Usage Guide
- TN1177, LatticeECP3 sysIO Usage Guide
- TN1178, LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide
- TN1179, LatticeECP3 Memory Usage Guide
- TN1180, LatticeECP3 High-Speed I/O Interface
- TN1181, Power Consumption and Management for LatticeECP3 Devices
- TN1182, LatticeECP3 sysDSP Usage Guide
- TN1184, LatticeECP3 Soft Error Detection (SED) Usage Guide
- TN1189, LatticeECP3 Hardware Checklist
- TN1215, LatticeECP2MS and LatticeECP2S Devices
- TN1216, LatticeECP2/M and LatticeECP3 Dual Boot Feature Advanced Security Encryption Key Programming Guide for LatticeECP3
- TN1222, LatticeECP3 Slave SPI Port User's Guide

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTL, LVCMOS, SSTL, HSTL): www.jedec.org
- PCI: www.pcisig.com

Date	Version	Section	Change Summary
			Updated Frequency to 150 Mbps in Table 3-11 Periodic Receiver Jitter Tolerance Specification
December 2010	01.7EA	Multiple	Data sheet made final. Removed “preliminary” headings.
			Removed data for 70E and 95E devices. A separate data sheet is available for these specific devices.
			Updated for Lattice Diamond design software.
		Introduction	Corrected number of user I/Os
		Architecture	Corrected the package type in Table 2-14 Available SERDES Quad per LatticeECP3 Devices.
			Updated description of General Purpose PLL
			Added additional information in the Flexible Quad SERDES Architecture section.
			Added footnotes and corrected the information in Table 2-16 Selectable master Clock (MCCLK) Frequencies During Configuration (Nominal).
			Updated Figure 2-16, Per Region Secondary Clock Selection.
			Updated description for On-Chip Programmable Termination.
			Added information about number of rows of DSP slices.
			Updated footnote 2 for Table 2-12, On-Chip Termination Options for Input Modes.
			Updated information for sysIO buffer pairs.
			Corrected minimum number of General Purpose PLLs (was 4, now 2).
		DC and Switching Characteristics	Regenerated sysCONFIG Port Timing figure.
			Added t_W (clock pulse width) in External Switching Characteristics table.
			Corrected units, revised and added data, and corrected footnote 1 in External Switching Characteristics table.
			Added Jitter Transfer figures in SERDES External Reference Clock section.
			Corrected capacitance information in the DC Electrical Characteristics table.
			Corrected data in the Register-to-Register Performance table.
			Corrected GDDR Parameter name HOGDDR.
			Corrected RSDS25 -7 data in Family Timing Adders table.
			Added footnotes 10-12 to DDR data information in the External Switching Characteristics table.
			Corrected titles for Figures 3-7 (DDR/DDR2/DDR3 Parameters) and 3-8 (Generic DDR/DDRX2 Parameters).
			Updated titles for Figures 3-5 (MLVDS25 (Multipoint Low Voltage Differential Signaling)) and 3-6 (Generic DDRX1/DDRX2 (With Clock and Data Edges Aligned)).
			Updated Supply Current table.
			Added GDDR interface information to the External Switching and Characteristics table.
			Added footnote to sysIO Recommended Operating Conditions table.
			Added footnote to LVDS25 table.
			Corrected DDR section footnotes and references.
			Corrected Hot Socketing support from “top and bottom banks” to “top and bottom I/O pins”.
		Pinout Information	Updated description for VTTx.